

Amendments to the Claims

This listing of claims replaces all previous versions and listings of the claims.

Listing of Claims:

1.-13. (Cancelled)

14. (Currently Amended) An article comprising a recrystallized ceramic material selected from the group consisting of silicon carbide, silicon nitride, and aluminum oxide, the ceramic material having a pore size of at least about 15 μm and comprising an active impurity component at a concentration of less than 1 ppm, wherein the impurity is one of iron, copper, nickel, chromium, and calcium.

15. (Currently Amended) The article of claim 14, wherein the active impurity ~~component~~ can migrate to a semiconductor wafer during semiconductor wafer processing.

16.-22. (Cancelled)

23. (Currently Amended) The article of claim 14, wherein the ~~ceramic material~~ silicon carbide further comprises ~~an inert impurity component~~ impurities.

24. (Currently Amended) The article of claim 14, wherein the article is a wafer boat ~~and the ceramic material comprises silicon carbide.~~

25.-29. (Cancelled)

30. (Currently Amended) An article comprising ~~a ceramic material with~~ recrystallized silicon carbide, ~~the ceramic material~~ having pores interconnected to form a network and comprising an active impurity component at a concentration of less than 1 ppm, wherein the active impurity component is one of iron, copper, nickel, chromium, and calcium.
31. (Currently Amended) The article of claim 30, wherein the article is a wafer boat ~~and the ceramic material comprises silicon carbide.~~
32. (Previously Presented) The article of claim 30 wherein the pores have a pore size of at least about 15 μm .
33. (Previously Presented) An article comprising a recrystallized silicon carbide member having a network of pores that have a pore size of at least about 5 μm .
34. (Currently Amended) The article of claim 33, wherein the silicon carbide member is free of free silicon.
35. (Previously Presented) The article of claim 33, wherein the silicon carbide member has a Fe concentration at or below 2 ppm.
36. (Previously Presented) The article of claim 33, wherein the silicon carbide member has a Ni concentration at or below 5 ppm.
37. (Previously Presented) The article of claim 33 wherein the silicon carbide member has an active impurity component at a concentration of less than about 400 ppm.

38. (New) A ceramic article comprising:
recrystallized silicon carbide having an interconnected network of pores with a pore size of at least about 5 μm ; and
an oxide layer on at least a portion of at least one surface of the ceramic article,
wherein the recrystallized silicon carbide has an impurity selected from the group consisting of iron, copper, nickel, chromium, and calcium, at a concentration of less than 1 ppm.
39. (New) The ceramic article of claim 38, wherein the recrystallized silicon carbide is free of free silicon.
40. (New) The ceramic article of claim 38, wherein the recrystallized silicon carbide has a pore surface area of less than about 0.04 m^2/gr .
41. (New) The ceramic article of claim 38, wherein the oxide layer comprises aluminum oxide.